



XFEL Read-out Amplifier Design

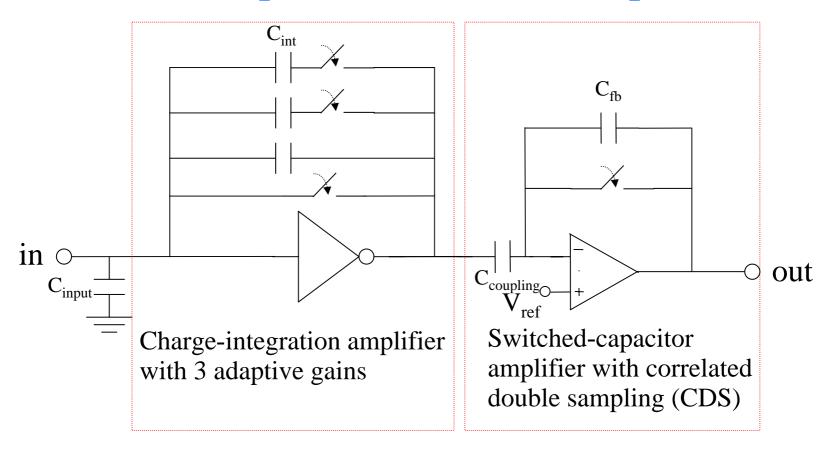
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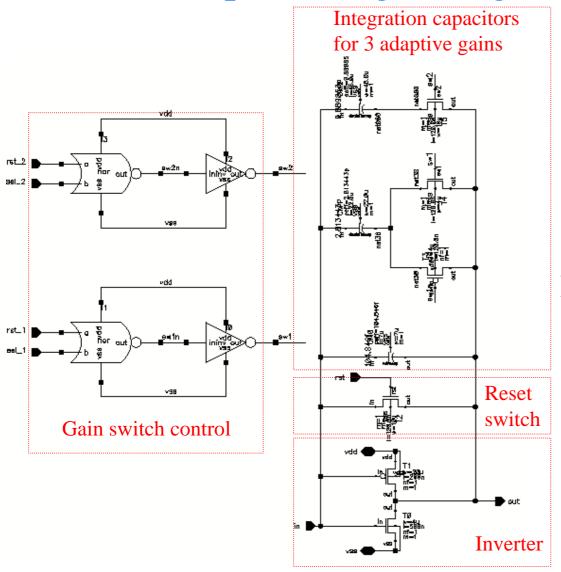
Concept of the read-out Amplifier







Input Charge Integration Amplifier



Voltage to charge gain:

$$\Delta V \ / \ Q = A_{dc} \ / \ (C_{input} + C_{int} \ + A_{dc} C_{int})$$

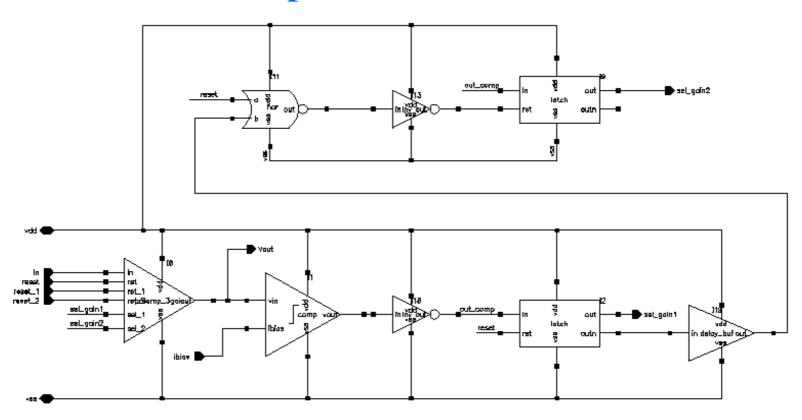
Main problems and solutions:

- > Charge injection => CDS
- > Input voltage peak => transmission gate as the switch for the intermediate gain stage.





Adaptive Gain Control



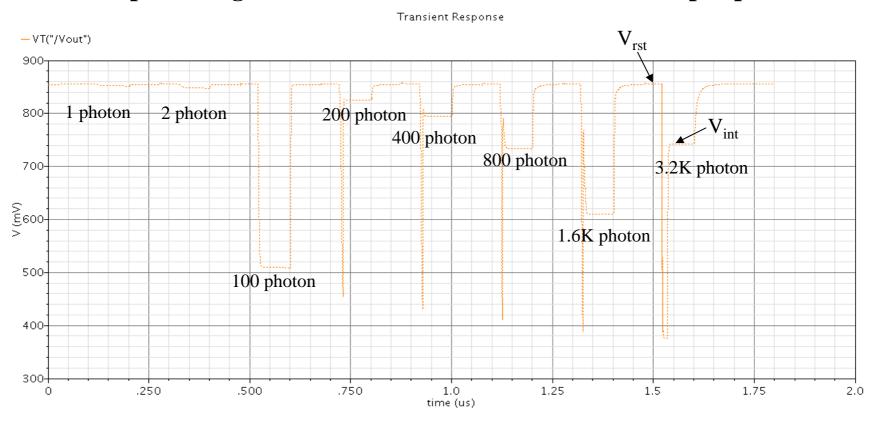
No accidental switching-on of the highest gain stage.





Simulation of the Input Amplifier

The output voltage waveform for different numbers of input photons

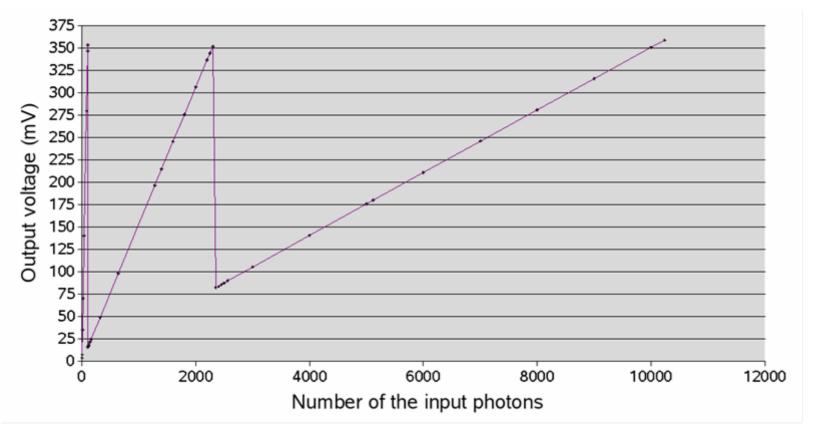


- > The maximal conversion gain: ~ 3.5 mV / photon (with 3k electron / photon).
- > Output noise: ~ 0.3 mV.





Simulation of the Input Charge Amplifier



The highest gain: ~ 3.5 mV / photon 1 - 102photons.

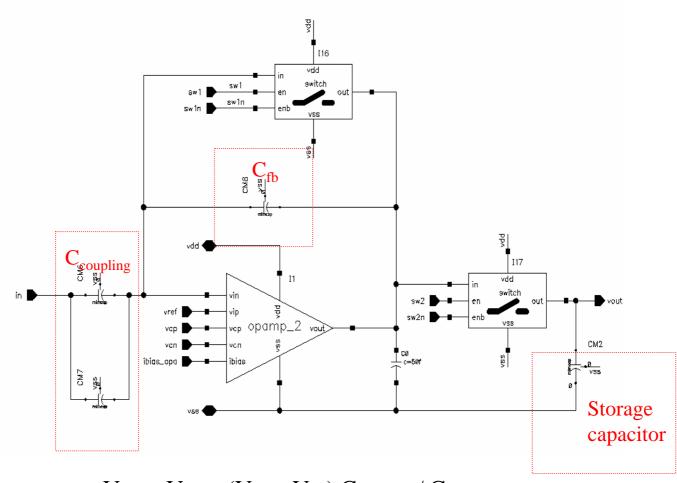
The medium gain: $\sim 0.15 \text{ mV} / \text{photon}$ 103 - 2300 photons.

> The lowest gain: $\sim 0.035 \text{ mV} / \text{photon}$ 2300 - 10000 photons.





Output Amplifier with CDS



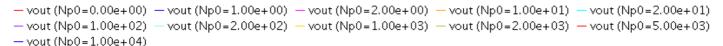
$$V_{\text{out}} = V_{\text{ref}} + (V_{\text{rst}} - V_{\text{int}}) C_{\text{coupling}} / C_{\text{fb}}$$

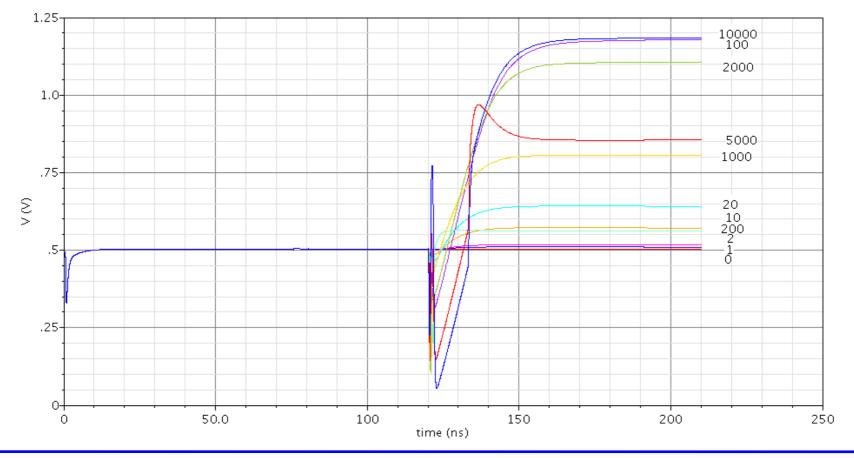




Simulation of the Output Amplifier

Transient Response





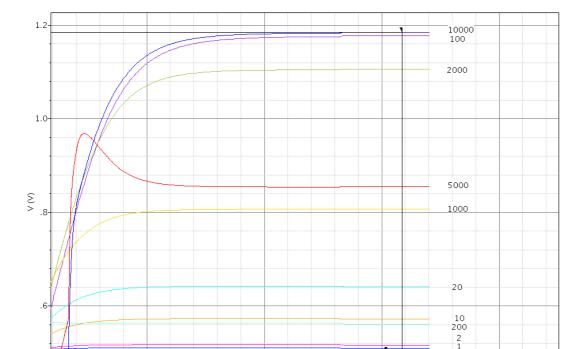




Simulation of the Output Amplifier

Transient Response

- vout (Np0=0.00e+00) - vout (Np0=1.00e+00) - vout (Np0=2.00e+00) - vout (Np0=2.00e+01) - vout (Np0=1.00e+01) - vout (Np0=1.00e+02) - vout (Np0=2.00e+02) - vout (Np0=1.00e+03) - vout (Np0=2.00e+03) - vout (Np0=2.00e+03) - vout (Np0=2.00e+04) - vout (Np0=1.00e+04)



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▼ 200.61ns 502.07mV ▼ 204.29ns 1.1848V

time (ns)

No. of Photon (mV)	$V_{out}(mV)$
1	6.95
2	13.91
10	69.62
20	139.46
100	675.19
200	59.48
1000	304.7
2000	604.35
5000	352.83
10000	682.47
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HPAD meeting, 07.10.2008 Xintian Shi

dx|dv 3.6818ns 682.74mV s

200





Conclusions

- > A read-out circuit is designed and simulated at the schematic level.
- ➤ The input stage is an charge-integration amplifier with 3-adptive gain.
- ➤ The output stage performs correlated double sampling (CDS).
- \triangleright Thanks to the adaptive gain, the input photon range can be 1 10⁴.
- ➤ The CDS operation effectively reduces the offset and low frequency noise.





Future works

- ➤ Optimize the circuit for minimizing the noise.
- > Extensive simulations for process, supply and temperature variation.
- Layout design with radiation tolerant technique, e.g. Enclosed layout transistor (ELT).





Questions?